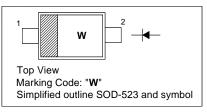
SILICON SCHOTTKY BARRIER DIODE

Features

- Low reverse current, low capacitance
- Ultra small flat package is suitable for surface mount design

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings $(T_a = 25 \, ^{\circ}C)$

Australia maximum ratings (1a = 20 °)					
Parameter	Symbol	Value	Unit		
Repetitive Peak Reverse Voltage	V_{RRM}	25	V		
Forward Current	I _F	50	mA		
Non-Repetitive Peak Forward Surge Current	I _{FSM}	200	mA		
Junction Temperature Range	T _j	125	°C		
Storage Temperature Range	Ts	- 55 to + 125	°C		

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 1 mA at I _F = 5 mA	V _F	0.33 0.38	>
Reverse Current at V _R = 20 V	I _R	0.45	μΑ
Capacitance at V _R = 1 V, f = 1 MHz	С	2.8	pF



listed on the Hong Kong Stock Exchange, Stock Code: 724)

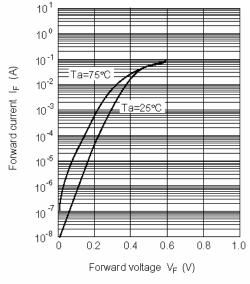


Fig.1 Forward current Vs. Forward voltage

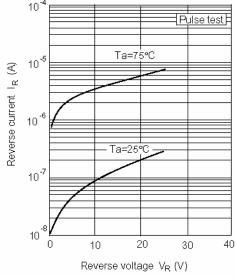


Fig.2 Reverse current Vs. Reverse voltage

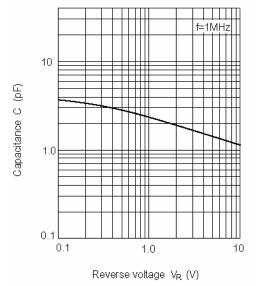


Fig.3 Capacitance Vs. Reverse voltage









PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523

